

SE6080GLB

N-Channel Enhancement-Mode MOSFET

Revision: A

General Description

This type used advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge.

- High density cell design for ultra low $R_{DS(ON)}$
- Excellent package for good heat dissipation

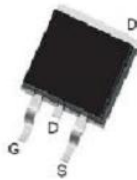
Features

For a single MOSFET

- $V_{DS} = 60V$
- $R_{DS(ON)} = 7m\Omega @ V_{GS}=10V$
-

Pin configurations

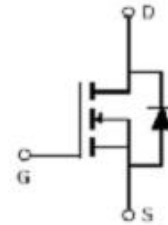
See Diagram below



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Absolute Maximum Ratings

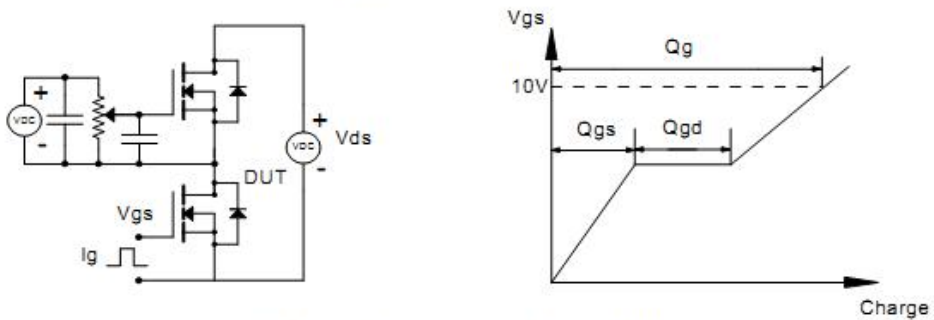
Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current	Continuous	80	A
	Pulsed	220	
Total Power Dissipation	@TA=25°C	110	W
Operating Junction Temperature Range	T_J	-55 to 175	°C

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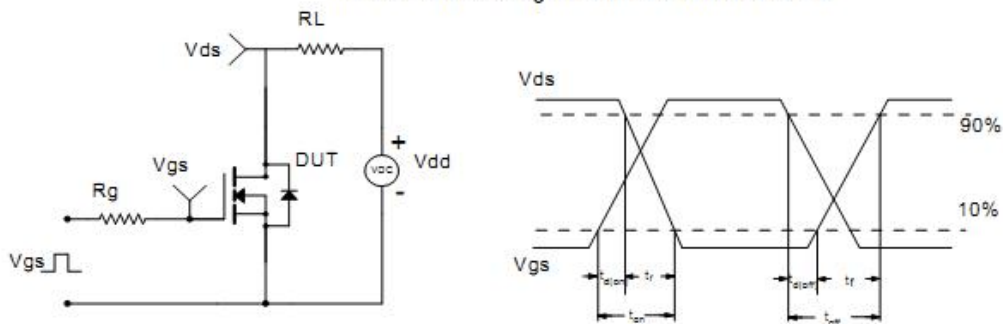
Electrical Characteristics (T _J =25°C unless otherwise noted)						
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS (Note 2)						
B _V DSS	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0 V	60			V
I _{DSS}	Drain to Source Leakage Current	V _{DS} = 48V, V _{GS} =0V			1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =20V			100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D =250μA	2		4	V
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =40A		7	8.5	mΩ
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =40V, f=1MHz		7765		pF
C _{oss}	Output Capacitance			960		pF
C _{rss}	Reverse Transfer Capacitance			66		pF
SWITCHING PARAMETERS						
Q _g	Total Gate Charge ²	V _{GS} =10V, V _{DS} =40V, I _D =20A		127	178	nC
Q _{gs}	Gate Source Charge			58		nC
Q _{gd}	Gate Drain Charge			35		nC
t _{d(on)}	Turn-On Delay Time	V _{GS} =10V, V _{DS} =40V, R _{GEN} =3Ω		24		ns
t _{d(off)}	Turn-Off Delay Time			55		ns
t _{d(r)}	Turn-On Rise Time			18		ns
t _{d(f)}	Turn-Off Fall Time			17		ns
Thermal Resistance						
Symbol	Parameter	Min	Typ	Units		
R _{θJC}	Junction to Case	0.35	0.55	°C/W		

Test Circuit

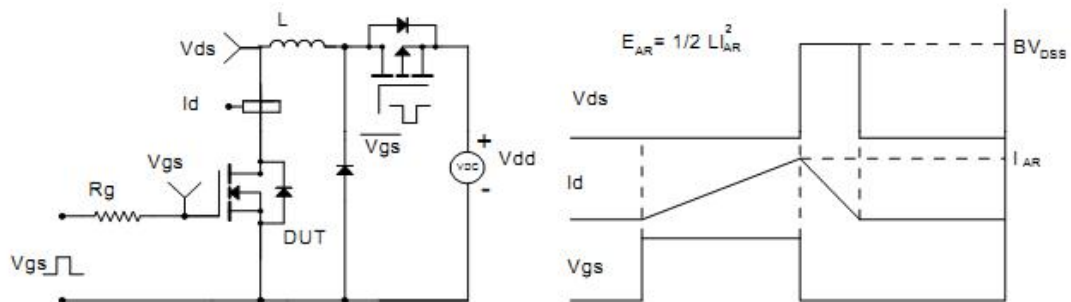
Gate Charge Test Circuit & Waveform



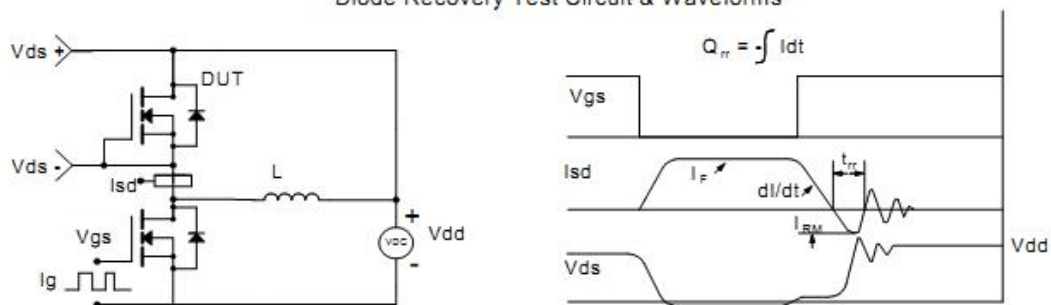
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Typical Characteristics

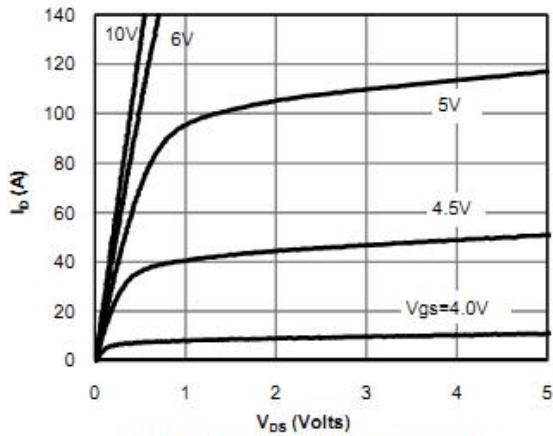


Fig 1: On-Region Characteristics (Note E)

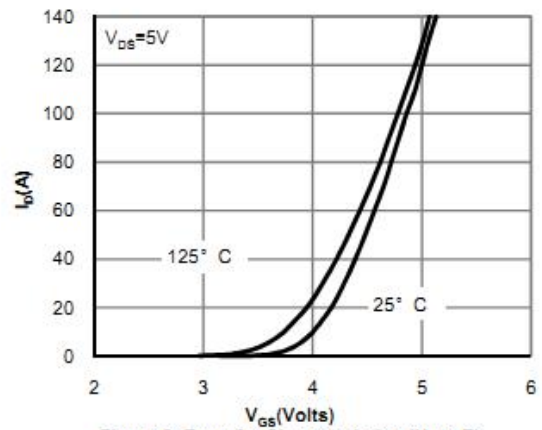


Figure 2: Transfer Characteristics (Note E)

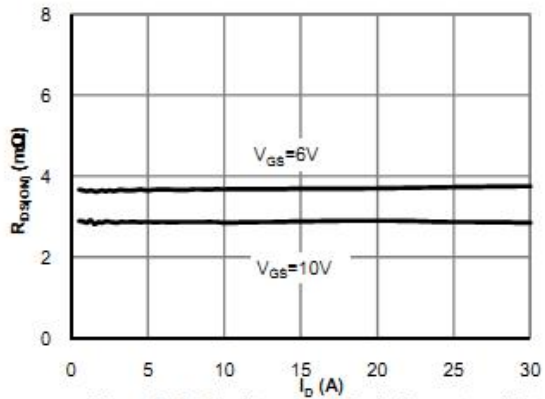


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

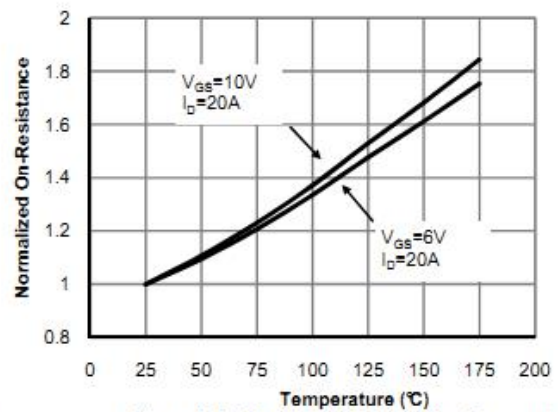


Figure 4: On-Resistance vs. Junction Temperature (Note E)

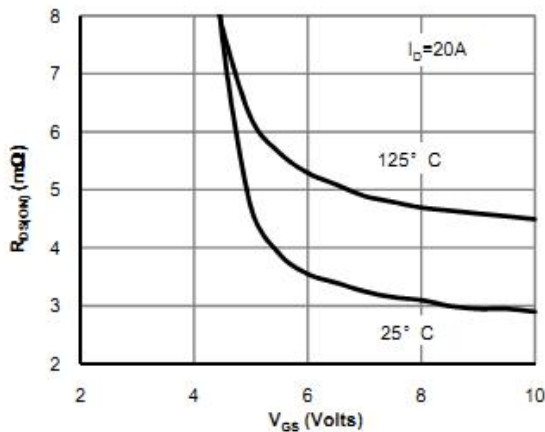


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

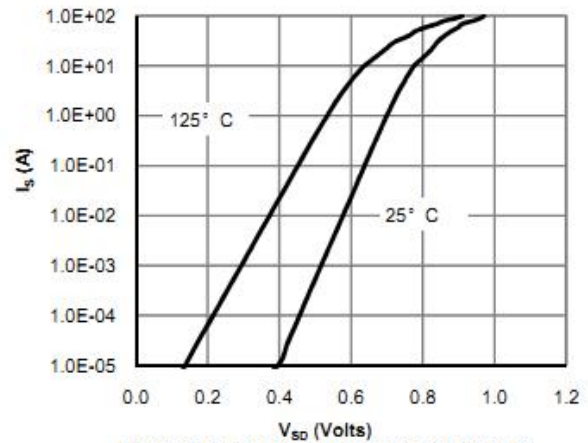


Figure 6: Body-Diode Characteristics (Note E)

Typical Characteristics

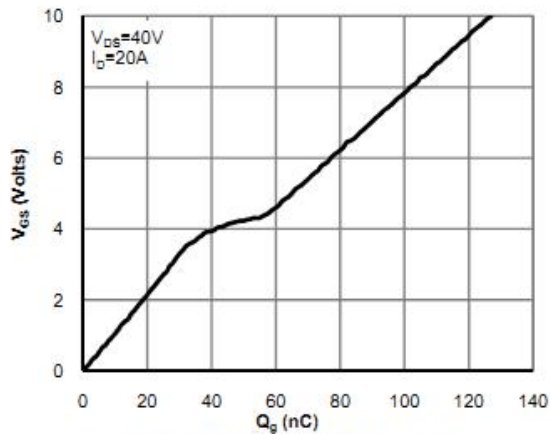


Figure 7: Gate-Charge Characteristics

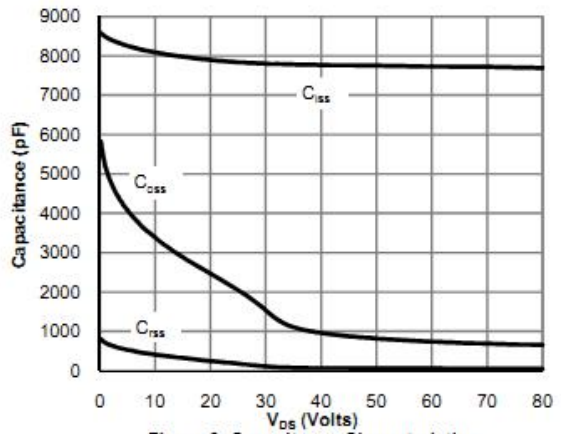


Figure 8: Capacitance Characteristics

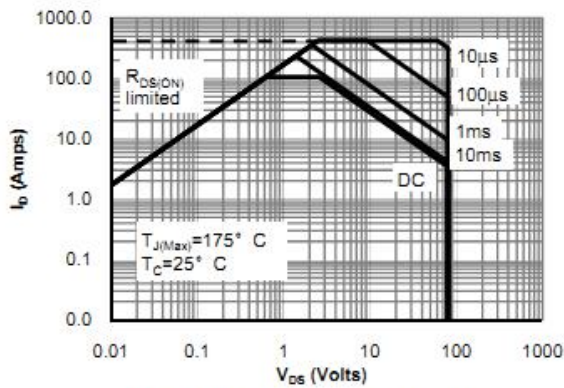


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

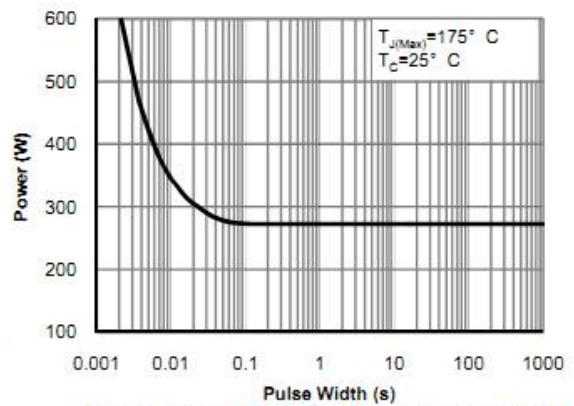


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

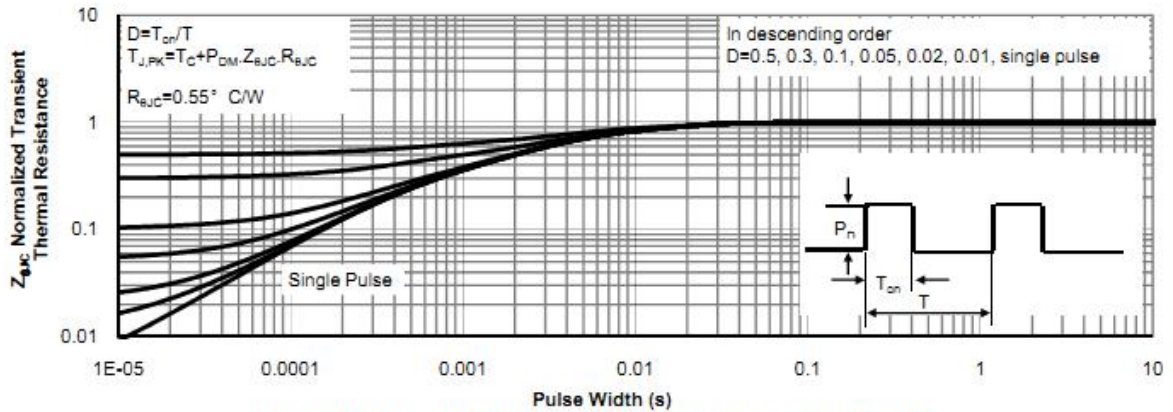


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

Typical Characteristics

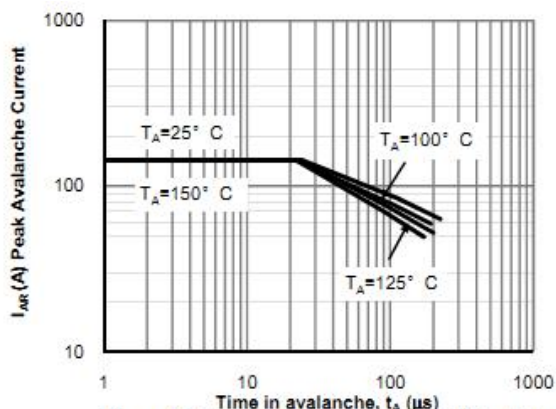


Figure 12: Single Pulse Avalanche capability (Note C)

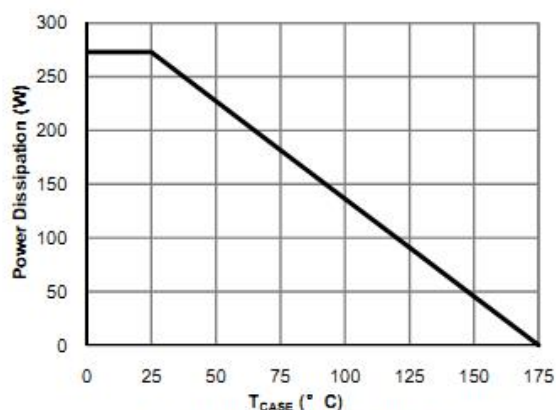


Figure 13: Power De-rating (Note F)

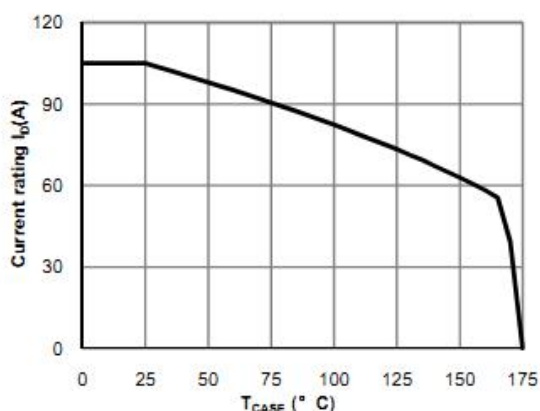


Figure 14: Current De-rating (Note F)

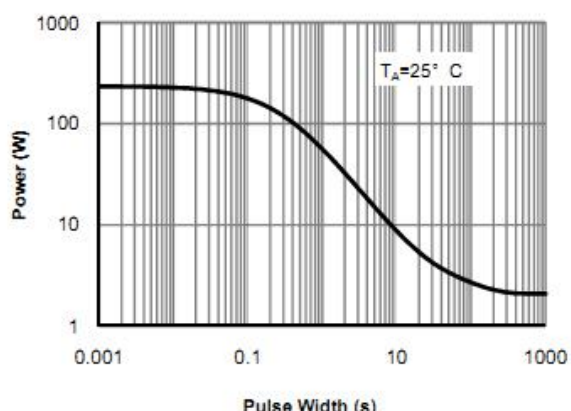


Figure 15: Single Pulse Power Rating Junction-to-Ambient (Note H)

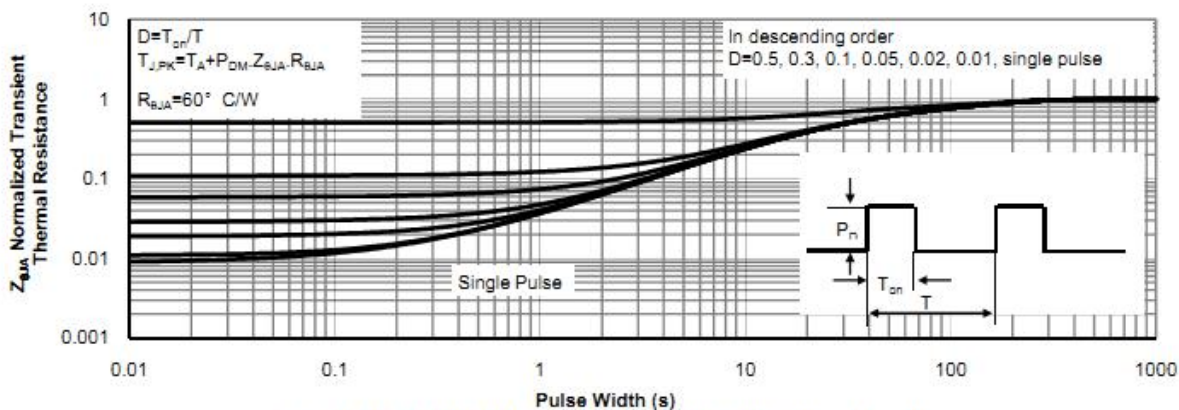
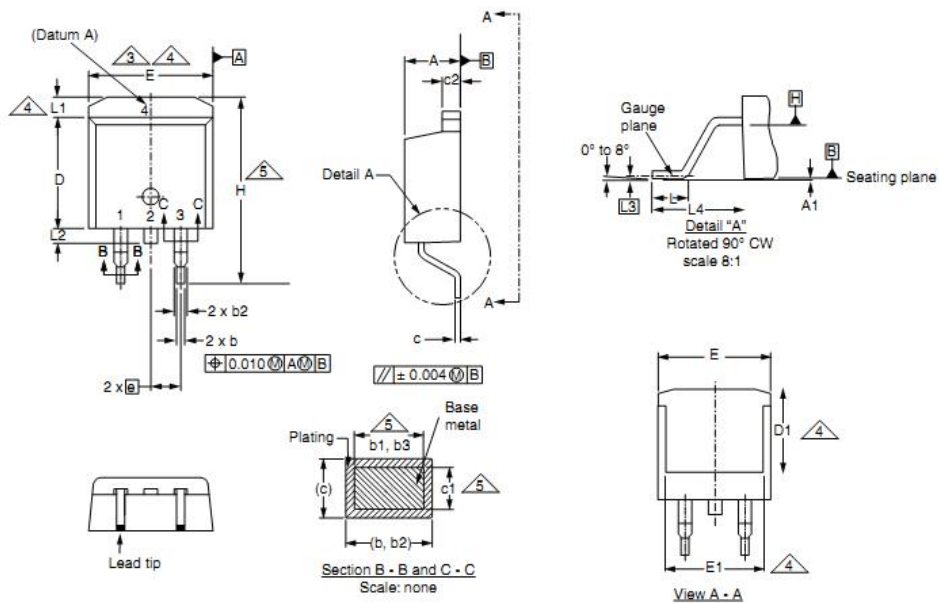


Figure 16: Normalized Maximum Transient Thermal Impedance (Note H)

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Package Outline Dimension

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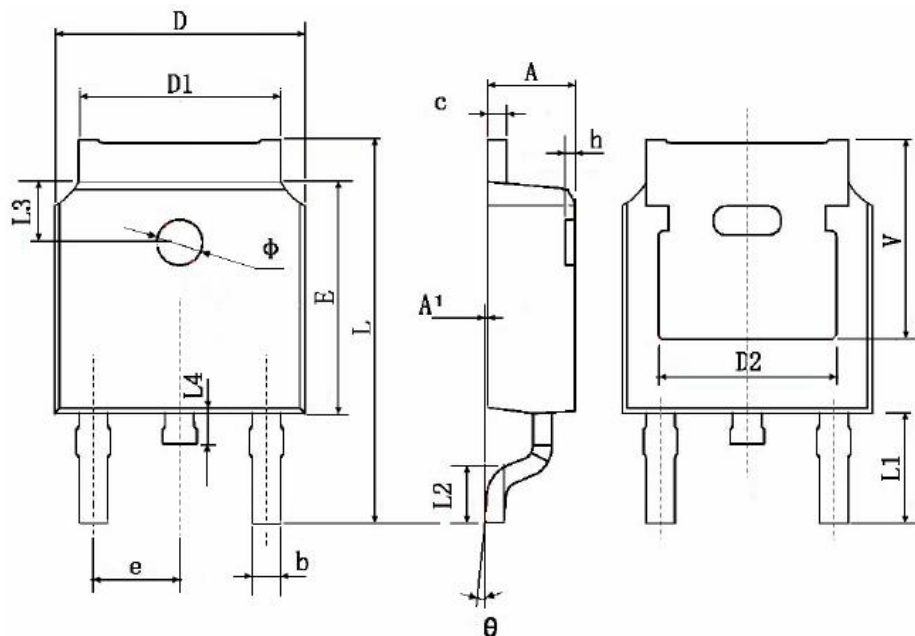
DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.06	4.83	0.160	0.190
A1	0.00	0.25	0.000	0.010
b	0.51	0.99	0.020	0.039
b1	0.51	0.89	0.020	0.035
b2	1.14	1.78	0.045	0.070
b3	1.14	1.73	0.045	0.068
c	0.38	0.74	0.015	0.029
c1	0.38	0.58	0.015	0.023
c2	1.14	1.65	0.045	0.065
D	8.38	9.65	0.330	0.380

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
D1	6.86	-	0.270	-
E	9.65	10.67	0.380	0.420
E1	6.22	-	0.245	-
e	2.54 BSC		0.100 BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	-	1.65	-	0.066
L2	-	1.78	-	0.070
L3	0.25 BSC		0.010 BSC	
L4	4.78	5.28	0.188	0.208

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Package Outline Dimension

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Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	

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